

1.0 Features

- Dual phase-locked loop (PLL) device with three output clock frequencies
- 3.3V supply voltage
- Small circuit board footprint (8-pin 0.150" SOIC)
- Custom frequency selections available contact your local AMI Sales Representative for more information

Figure 1: Pin Configuration



2.0 Description

The FS6282 is a monolithic CMOS clock generator IC designed to minimize cost and component count in digital video/audio systems.

Two high-resolution phase-locked loops generate two output clocks (CLKA and CLKB) through an array of postdividers. All frequencies are ratiometrically derived from the crystal oscillator frequency. The locking of all the output frequencies together can eliminate unpredictable artifacts in video systems and reduce electromagnetic interference (EMI) due to frequency harmonic stacking.

Table 1: Crystal / Output Frequencies

DEVICE	f _{XIN} (MHz)	CLKA (MHz)	CLKB (MHz)	CLKC (MHz)		
FS6282-03	20.000	20.000	48.000	8.000		
TE: Contact AMI for quotom BLL frequencies						

NOTE: Contact AMI for custom PLL frequencies

Figure 2: Block Diagram



This document contains information on a preproduction product. Specifications and information herein are subject to change without notice.



Table 2: Pin Descriptions

Key: AI = Analog Input; AO = Analog Output; DI = Digital Input; DI^U = Input with Internal Pull-Up; DI_D = Input with Internal Pull-Down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input, DO = Digital Output; P = Power/Ground; # = Active Low pin

PIN	TYPE	NAME	DESCRIPTION
1	DO	CLKA	Clock Output A
2	Р	VSS	Ground
3	AI	XIN	Crystal Oscillator Feedback
4	AO	XOUT	Crystal Oscillator Drive
5	DO	CLKB	Clock Output B
6	DO	CLKC	Clock Output C
7	Р	VDD	Power (+3.3 volts)
8	DI ^U	OE	Output Enable (outputs active when OE=VDD)

3.0 Electrical Specifications

Table 3: Absolute Maximum Ratings

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only, and functional operation of the device at these or any other conditions above the operational limits noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality, and reliability.

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage (V _{SS} = ground)	V _{DD}	V _{SS} -0.5	7	V
Input Voltage, dc	VI	V _{SS} -0.5	V _{DD} +0.5	V
Output Voltage, dc	Vo	V _{SS} -0.5	V _{DD} +0.5	V
Input Clamp Current, dc ($V_1 < 0$ or $V_1 > V_{DD}$)	Ι _{ικ}	-50	50	mA
Output Clamp Current, dc ($V_1 < 0$ or $V_1 > V_{DD}$)	Ι _{οκ}	-50	50	mA
Storage Temperature Range (non-condensing)	Ts	-65	150	°C
Ambient Temperature Range, Under Bias	T _A	-55	125	°C
Junction Temperature	TJ		125	°C
Lead Temperature (soldering, 10s)			260	°C
Input Static Discharge Voltage Protection (MIL-STD 883E, Method 3015.7)			2	kV



CAUTION: ELECTROSTATIC SENSITIVE DEVICE

Permanent damage resulting in a loss of functionality or performance may occur if this device is subjected to a high-energy electrostatic discharge.

Table 4: Operating Conditions

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Supply Voltage	V _{DD}	3.3V ± 10%	3.0	3.3	3.6	V
Ambient Operating Temperature Range	T _A		0		70	°C



Table 5: DC Electrical Specifications

Unless otherwise stated, $V_{DD} = 3.3V \pm 10\%$, no load on any output, and ambient temperature range $T_A = 0^{\circ}C$ to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are $\pm 3\sigma$ from typical. Negative currents indicate current flows out of the device.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS		
Overall								
Supply Current, Dynamic, with Loaded Outputs	I _{DD}	$f_{XTAL} = 13.5 MHz; C_L = 10 pF, V_{DD} = 3.6 V$		30		mA		
Crystal Oscillator								
Crystal Loading Capacitance	$C_{L(xtal)}$	As seen by a crystal connected to XIN and XOUT		18		pF		
Clock Outputs (CLKA, CLKB)	Clock Outputs (CLKA, CLKB)							
Quitout Impodance *	Z _{OH}	$V_{O} = 0.1 V_{DD}$; output driving high		45		0		
Output impedance	Z _{OL}	$V_{O} = 0.1 V_{DD}$; output driving low 45						
Short Circuit Source Current *	I _{OSH}	$V_{O} = 0V$; shorted for 30s, max.		-35		mA		
Short Circuit Sink Current *	I _{OSL}	$V_0 = 3.3V$; shorted for 30s, max.		35		mA		

Table 6: AC Timing Specifications

Unless otherwise stated, V_{DD} = 3.3V ± 10%, no load on any output, and ambient temperature range T_A = 0°C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are ±3 σ from typical.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION MIN.		TYP.	MAX.	UNITS		
Overall								
Synthesis Error		(unless otherwise noted in Frequency Table)			0	ppm		
Clock Outputs (CLKA, CLKB, CLKC)								
Duty Cycle *		Ratio of high pulse width (as measured from rising edge to next falling edge at $V_{\rm DD}/2$) to one clock period	45		55	%		
Jitter, Period (peak-peak) *	$t_{j(\Delta P)}$	From rising edge to next rising edge at $V_{DD}/2$, $C_L = 10 pF$		300		ps		
Rise Time *	tr	V_{DD} = 3.3V; V_{O} = 0.3V to 3.0V; C_{L} = 10pF		3		ns		
Fall Time *	t _f	V_{DD} = 3.3V; V_{O} = 3.0V to 0.3V; C_{L} = 10pF		2.5		ns		



4.0 Package Information

Table 7: 8-pin SOIC (0.150") Package Dimensions

	DIMENSIONS						
	INC	HES	MILLIM	ETERS			
	MIN.	MAX.	MIN.	MAX.			
А	0.061	0.068	1.55	1.73			
A1	0.004	0.0098	0.102	0.249			
A2	0.055	0.061	1.40	1.55			
В	0.013	0.019	0.33	0.49			
С	0.0075	0.0098	0.191	0.249			
D	0.189	0.196	4.80	4.98			
Е	0.150	0.157	3.81	3.99			
е	0.050	BSC	1.27	BSC			
Н	0.230	0.244	5.84	6.20			
h	0.010	0.016	0.25	0.41			
L	0.016	0.035	0.41	0.89			
Θ	0°	8°	0°	8°			



Table 8: 8-pin SOIC (0.150") Package Characteristics

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	TYP.	UNITS	
Thermal Impedance, Junction to Free-Air 8-pin 0.150" SOIC	Θ_{JA}	Air flow = 0 m/s	110	°C/W	
Lood Inductorian Colf	L ₁₁	Corner lead	2.0	nH	
Lead Inductance, Sen		Center lead	1.6		
Lead Inductance, Mutual	L ₁₂	Any lead to any adjacent lead	0.4	nH	
Lead Capacitance, Bulk	C ₁₁	Any lead to V_{SS}	0.27	pF	



5.0 Ordering Information

ORDERING CODE	DEVICE NUMBER	PACKAGE TYPE	OPERATING TEMPERATURE RANGE	SHIPPING CONFIGURATION
11640-828	FS6282-03	8-pin (0.150") SOIC (Small Outline Package)	0° C to 70° C (Commercial)	Tape and Reel
11640-838	FS6282-03	8-pin (0.150") SOIC (Small Outline Package)	0° C to 70° C (Commercial)	Tubes

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